Blakely, Sokoloff, Taylor & Zafman LLP (408) 720-8300 Title: BIPOLAR JUNCTION TRANSISTOR WITH IMPROVED EXTRINSIC BASE REGION AND METHOD OF FABRICATION

1st Named Inventor: Shahriar Ahmed

Express Mail No.: EV627467331US Docket No.: 42P17289

Sheet: 1 of 6

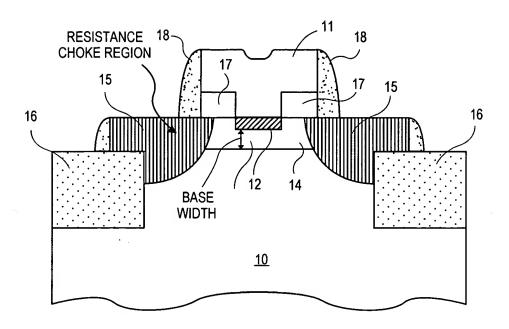


FIG. 1 (PRIOR ART)

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Sheet: 2 of 6

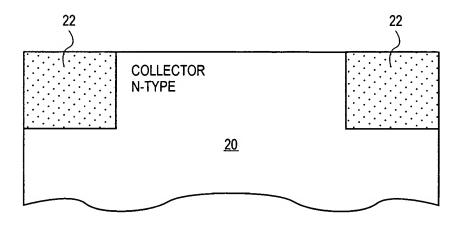


FIG. 2

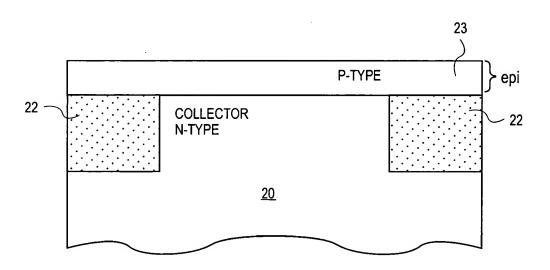


FIG. 3

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Docket No.: 42P17289

Sheet: 3 of 6

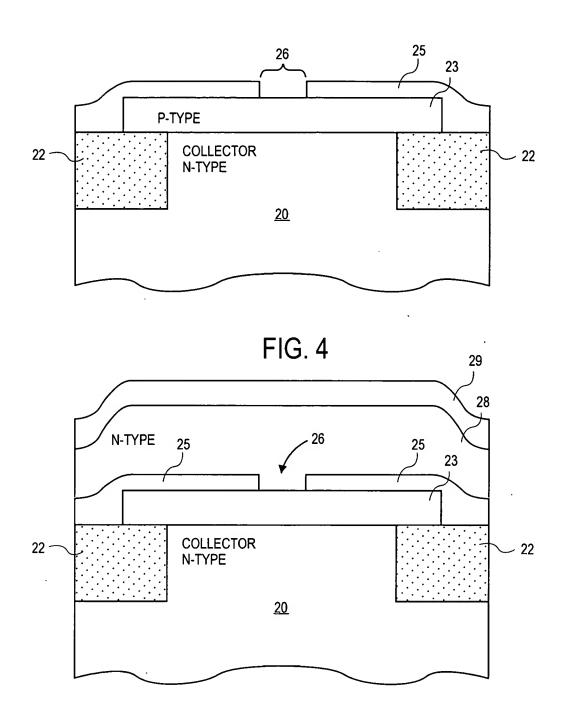


FIG. 5

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Express Mail No.: EV627467331US

Sheet: 4 of 6

Docket No.: 42P17289

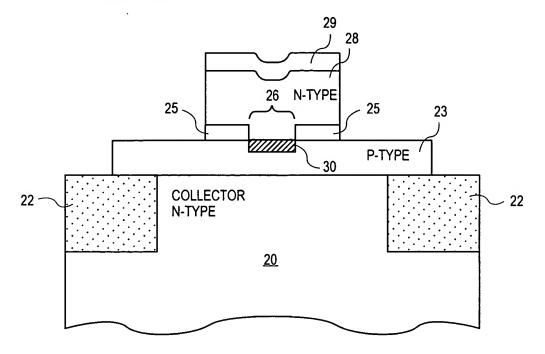


FIG. 6

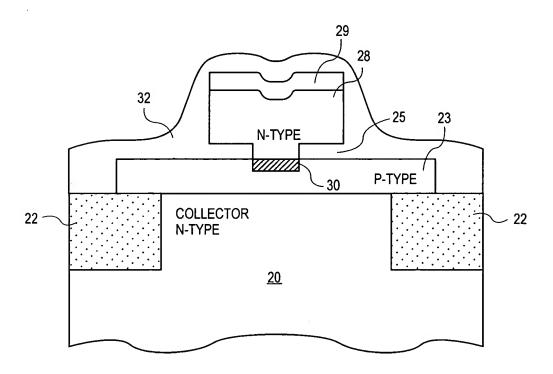


FIG. 7

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Docket No.: 42P17289

Sheet: 5 of 6

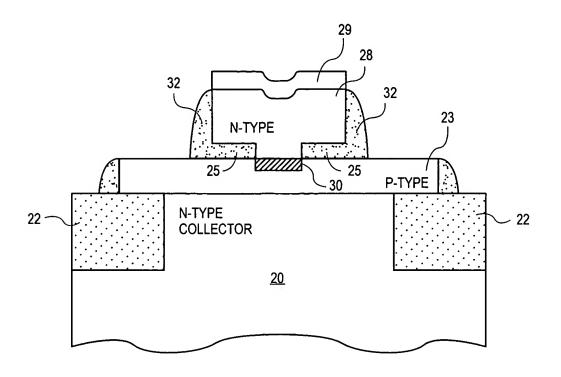


FIG. 8 29 28 N-TYPE 36 23 30 P-TYPE N-TYPE 22 22 **COLLECTOR** <u>20</u>

FIG. 9

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1st Named Inventor: Shahriar Ahmed

Express Mail No.: EV627467331US Sheet: 6 of 6

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Docket No.: 42P17289

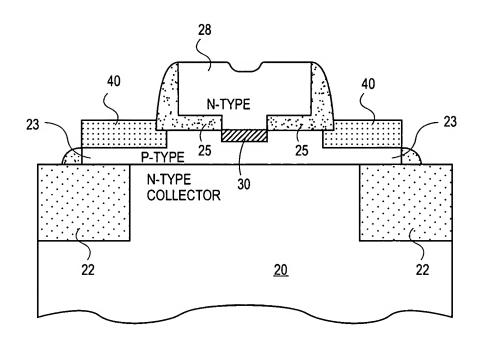


FIG. 10